# § 469.23

1.1.2 Trichloroethane dichlorobromomethane

- (b) The term "electronic crystals" means crystals or crystalline material which because of their unique structural and electronic properties are used in electronic devices. Examples of these crystals are crystals comprised of quartz, ceramic, silicon, gallium arsenide, and idium arsenide.
- (c) The term "manufacture of electronic crystals" means the growing of crystals and/or the production of crystal wafers for use in the manufacture of electronic devices.

[48 FR 15394, Apr. 8, 1983, as amended at 48 FR 45250, Oct. 4, 1983]

## § 469.23 Monitoring.

The certification alternative to monitoring for Total Toxic Organics (TTO) described in §469.13 (a), (b), (c), and (d) is applicable to this subpart.

(Approved by the Office of Management and Budget under control number 2040-0074)

[48 FR 15394, Apr. 8, 1983, as amended at 50 FR 4515, Jan. 31, 1985]

#### § 469.24 Effluent limitations resenting the degree of effluent reduction attainable by the application of the best practicable control technology currently available (BPT).

Except as provided in 40 CFR 125.30 through 32, any existing point source subject to this subpart must achieve the following effluent limitations representing the degree of effluent reduction attainable by the application of the best practicable control technology currently available (BPT):

SUBPART B-ELECTRONIC CRYSTALS BPT **EFFLUENT LIMITATIONS** 

Pollutant or pollutant property	Maximum for any 1 day	Average of daily values for 30 con- secutive days
	Milligrams per liter (mg/l)	
TTO <sup>1</sup> Arsenic (T) <sup>2</sup>	1.37 2.09	( <sup>3</sup> ) 0.83
Fluoride (T)	32.0	17.4
TSS	61.0	23.0
pH	(4)	(4)

<sup>1</sup>Total toxic organics. <sup>2</sup>The arsenic (T) limitation only applies to manufacturers of gallium or indium arsenide crystals

§ 469.25 Effluent limitations resenting the degree of effluent reduction attainable by the application of the best available technology economically achievable (BAT).

Except as provided in 40 CFR 125.30 through 32, any existing point source subject to this subpart must achieve the following effluent limitations representing the degree of effluent reduction attainable by the application of the best available technology economically available (BAT):

SUBPART B-ELECTRONIC CRYSTALS BAT **EFFLUENT LIMITATIONS** 

Pollutant or pollutant property	Maximum for any 1 day	Average of daily values for 30 con- secutive days
	Milligrams per liter (mg/l)	
TTO¹ Arsenic² Fluoride	1.37 2.09 32.0	( <sup>3</sup> ) 0.83 17.4

<sup>&</sup>lt;sup>1</sup> Total toxic organics.

### 3 Not applicable.

## §469.26 Pretreatment standards for existing sources (PSES).

(a) Except as provided in 40 CFR 403.7 and 403.13, any existing source subject to this subpart which introduces pollutants into a publicly owned treatment works must comply with 40 CFR part 403 and achieve the following pretreatment standards for existing sources (PSES):

SUBPART B-ELECTRONIC CRYSTALS PSES **EFFLUENT LIMITATIONS** 

Pollutant or pollutant property	Maximum for any 1 day	Average of daily values for 30 con- secutive days
	Milligrams per liter (mg/l)	
TTO <sup>1</sup>	1.37 2.09	(²) 0.83

<sup>&</sup>lt;sup>1</sup> Total toxic organics.

(b) An existing source submitting a certification in lieu of monitoring pursuant to §469.13 (c) and (d) of this regulation must implement the solvent

<sup>&</sup>lt;sup>3</sup>Not applicable. <sup>4</sup>Within the range of 6.0 to 9.0.

 $<sup>^2\</sup>mbox{The}$  arsenic limitation only applies to manufacturers of gallium or indium arsenide crystals.

<sup>&</sup>lt;sup>2</sup> Not applicable.

<sup>&</sup>lt;sup>3</sup>The arsenic (T) limitation only applies to manufacturers of gallium or indium arsenide crystals.